

In the Specification:

Kindly amend the specification as indicated.

Page 14, Paragraph 35, please amend as follows:

According to the present invention, a thin lower adhesion-promoting layer 44 formed from either Si_xC_y , Si_xN_y , or SiCN having a thickness of about 2 angstroms to about 20 angstroms, or other suitable adhesion-promoting layer, as described above, is disposed over the lower Ti barrier metal layer 42 lying on the tungsten plug 40. An antifuse material layer 46 of amorphous carbon or amorphous carbon doped with hydrogen and having a thickness of about 2.5 nm to about 1000 nm is disposed over the lower adhesion-promoting layer 44. A thin upper adhesion-promoting layer 48 formed from either Si_xC_y , Si_xN_y , SiCN having a thickness of about 2 angstroms to about 20 angstroms, or other suitable adhesion-promoting layer, as described above, is disposed over antifuse material layer-44-46.

Page 15, Paragraph 36, please amend as follows:

A Ti barrier metal layer 50 forming an upper antifuse electrode having a thickness of about 25 nm to about 200 nm is disposed over the adhesion-promoting layer 48. A hard mask layer 52 is deposited over barrier metal layer 48. In FIG. 2B, the hardmask layer is formed ~~form~~from an insulating material such as silicon dioxide, and in FIG. 2A, the hardmask layer is formed from W.